BAS70-04LT1

Preferred Device

Dual Series Schottky Barrier Diode

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Features

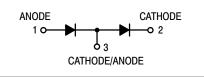
- Extremely Fast Switching Speed
- Low Forward Voltage
- Pb–Free Package is Available



ON Semiconductor®

http://onsemi.com

70 VOLTS SCHOTTKY BARRIER DIODE



MAXIMUM RATINGS (T_J = 150°C unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	70	Volts

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Forward Power Dissipation @ T _A = 25°C Derate above 25°C	P _F	225 1.8	mW mW/°C
Operating Junction and Storage Temperature Range	T _J , T _{stg}	–55 to +150	°C



TO-236AB CASE 318

MARKING DIAGRAM



CG = Specific Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
BAS70-04LT1	SOT-23	3000 / Tape & Reel
BAS70-04LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

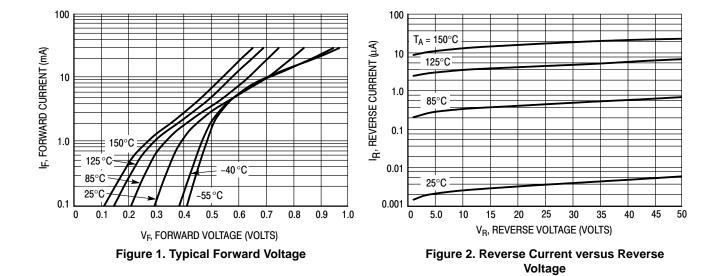
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

BAS70-04LT1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage (I _R = 10 μ A)	V _{(BR)R}	70	—	Volts
Total Capacitance (V _R = 0 V, f = 1.0 MHz)	C _T	-	2.0	pF
Reverse Leakage ($V_R = 50 \text{ V}$) ($V_R = 70 \text{ V}$)	۱ _R	_	0.1 10	μAdc
Forward Voltage (I _F = 1.0 mAdc)	V _F	-	410	mVdc
Forward Voltage (I _F = 10 mAdc)	V _F	-	750	mVdc
Forward Voltage (I _F = 15 mAdc)	V _F	-	1.0	Vdc



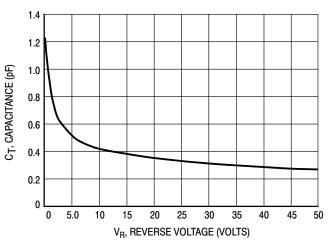


Figure 3. Typical Capacitance

PACKAGE DIMENSIONS

SOT-23 (TO-236AB) PLASTIC PACKAGE CASE 318-08 **ISSUE AI**



DIMENSIONING AND TOLERANCING PER ANSI Y14,5M, 1982.
CONTROLLING DIMENSION: INCH.
MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
CORPOLETE NEW STANDARD

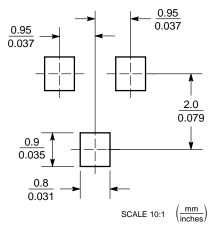
4. 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.1102	0.1197	2.80	3.04
В	0.0472	0.0551	1.20	1.40
С	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
Н	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
Κ	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

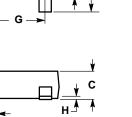
STYLE 11: PIN 1. ANODE 2. CATHODE

3. CATHODE-ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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BAS70-04LT1

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